

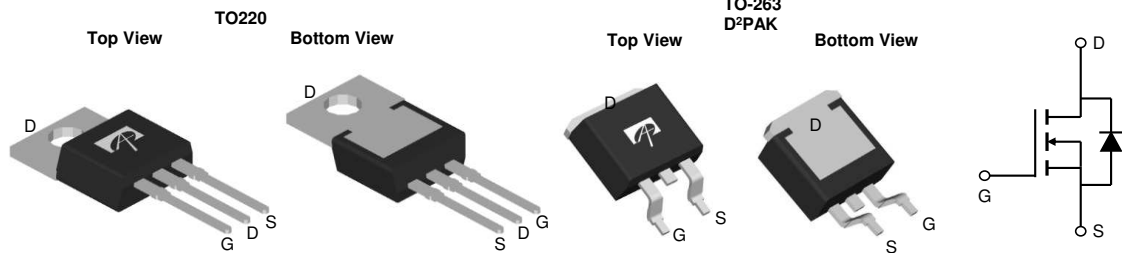
General Description

The AOT284L & AOB284L uses trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$, C_{iss} and C_{oss} . This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Product Summary

V_{DS}	80V
I_D (at $V_{GS}=10V$)	105A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	$< 4.5m\Omega$ ($< 4.3m\Omega^*$)
$R_{DS(ON)}$ (at $V_{GS}=6V$)	$< 5.7m\Omega$ ($< 5.5m\Omega^*$)

100% UIS Tested
100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	105	A
$T_C=25^\circ C$		82	
$T_C=100^\circ C$			
Pulsed Drain Current ^C	I_{DM}	400	
Continuous Drain Current	I_{DSM}	16	A
$T_A=25^\circ C$		12.5	
$T_A=70^\circ C$			
Avalanche Current ^C	I_{AS}	65	A
Avalanche energy $L=0.1mH$ ^C	E_{AS}	211	mJ
Power Dissipation ^B	P_D	250	W
$T_C=25^\circ C$		125	
$T_C=100^\circ C$			
Power Dissipation ^A	P_{DSM}	2.1	W
$T_A=25^\circ C$		1.3	
$T_A=70^\circ C$			
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	12	15	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JC}$	48	60	$^\circ C/W$
Steady-State				
Maximum Junction-to-Case	$R_{\theta JC}$	0.45	0.6	$^\circ C/W$
Steady-State				

* Surface mount package TO263

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	80			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=80\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.3	2.8	3.3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	400			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=20\text{A}$ TO220 $T_J=125^\circ\text{C}$		3.6 5.8	4.5 7.2	m Ω
		$V_{GS}=6\text{V}$, $I_D=20\text{A}$ TO220		4.4	5.7	
		$V_{GS}=10\text{V}$, $I_D=20\text{A}$ TO263		3.4	4.3	
		$V_{GS}=6\text{V}$, $I_D=20\text{A}$ TO263		4.2	5.5	
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=20\text{A}$		80		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.69	1	V
I_S	Maximum Body-Diode Continuous Current ^G				105	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=40\text{V}$, $f=1\text{MHz}$		5154		pF
C_{oss}	Output Capacitance			673		pF
C_{rss}	Reverse Transfer Capacitance			48		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$	0.4	0.8	1.2	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=40\text{V}$, $I_D=20\text{A}$		71	100	nC
Q_{gs}	Gate Source Charge			18.5		nC
Q_{gd}	Gate Drain Charge			11.5		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=40\text{V}$, $R_L=2\Omega$, $R_{GEN}=3\Omega$		18		ns
t_r	Turn-On Rise Time			11		ns
$t_{D(off)}$	Turn-Off DelayTime			38		ns
t_f	Turn-Off Fall Time			9		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$		38		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$		230		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

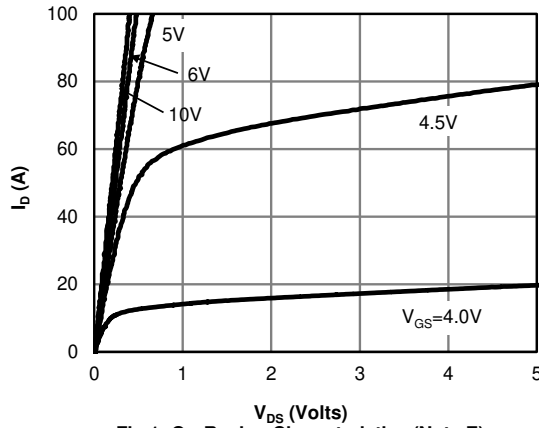


Fig 1: On-Region Characteristics (Note E)

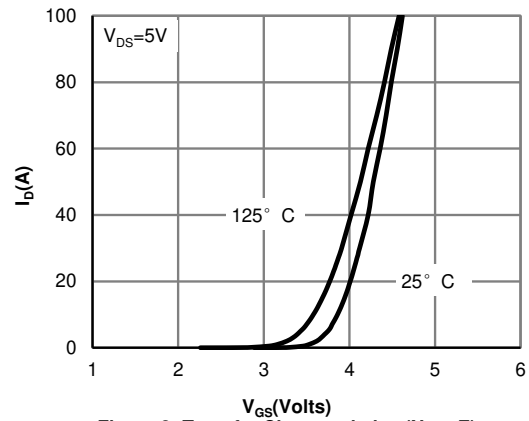


Figure 2: Transfer Characteristics (Note E)

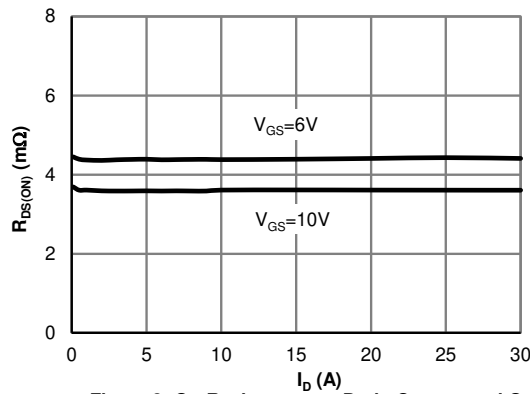


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

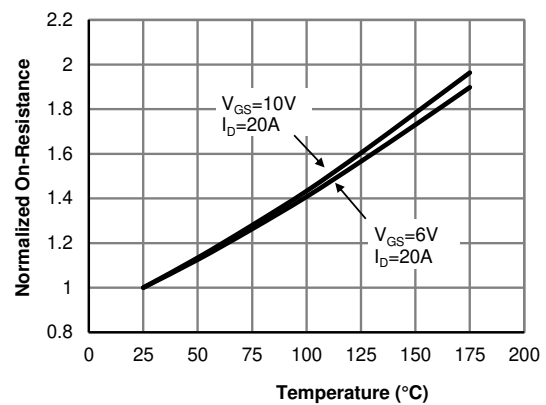


Figure 4: On-Resistance vs. Junction Temperature (Note E)

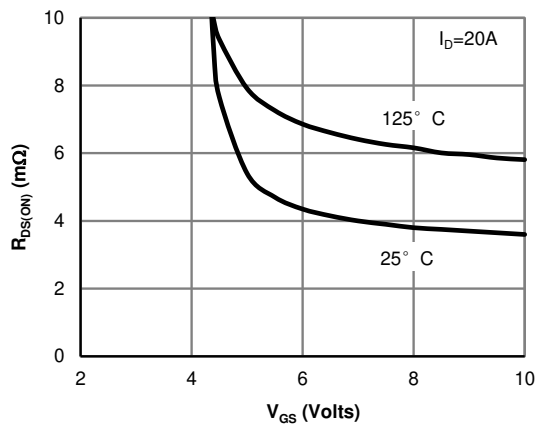


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

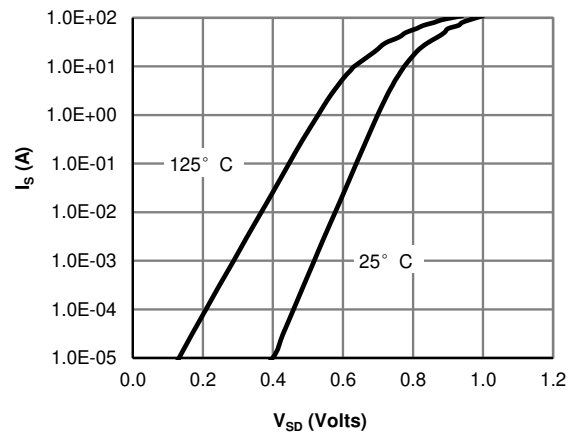
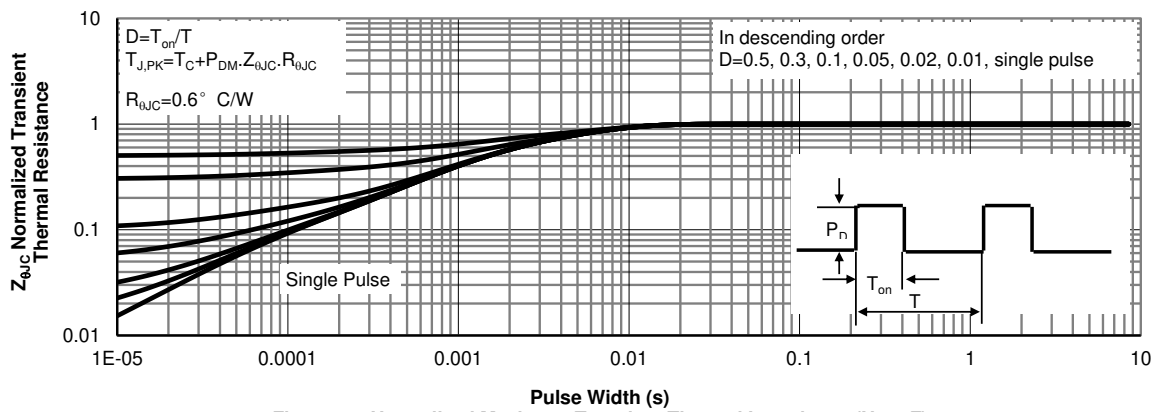
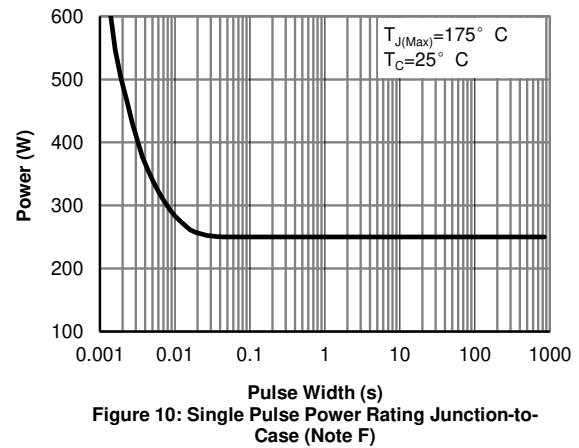
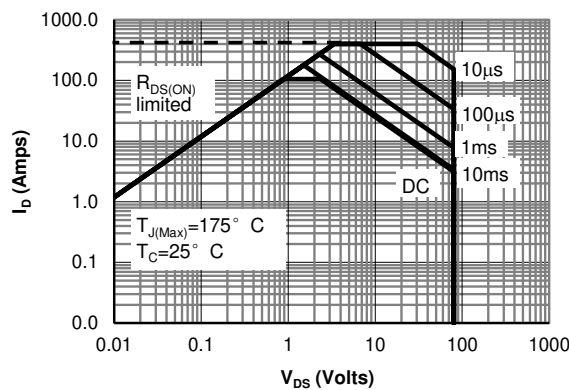
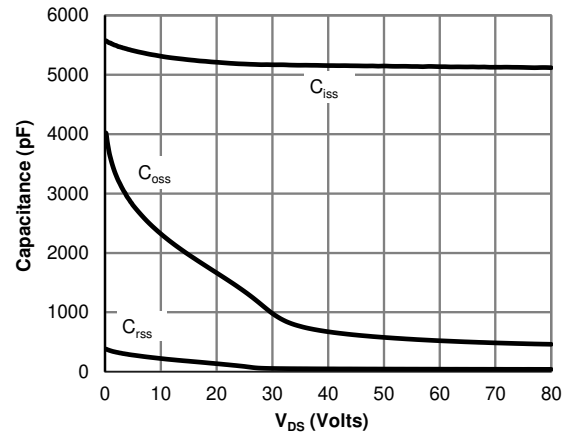
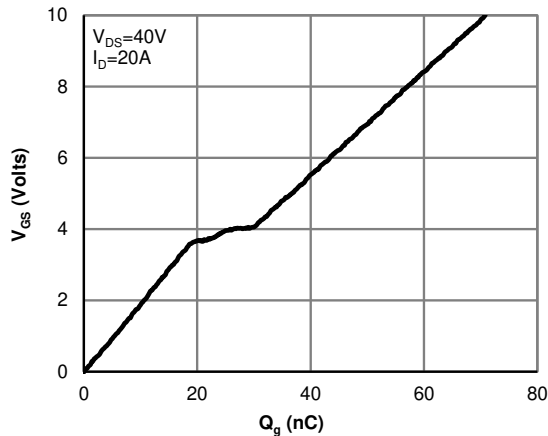


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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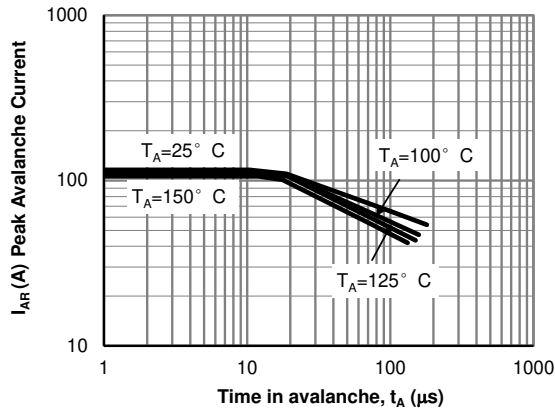


Figure 12: Single Pulse Avalanche capability (Note C)

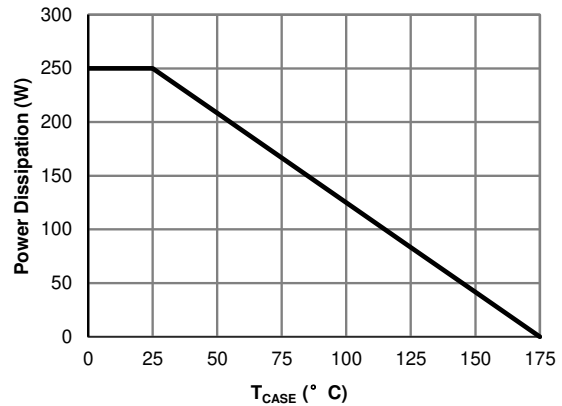


Figure 13: Power De-rating (Note F)

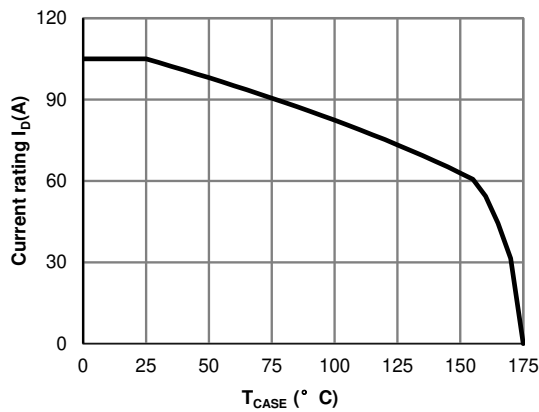


Figure 14: Current De-rating (Note F)

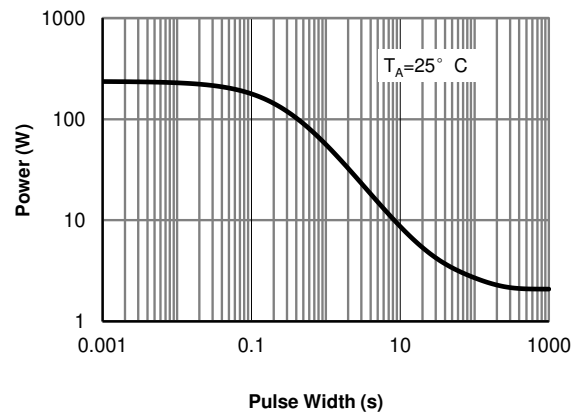


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

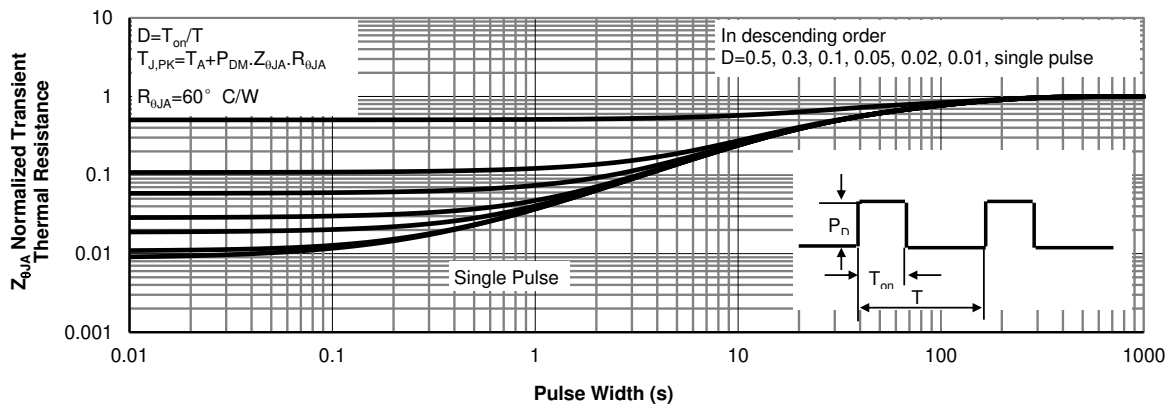
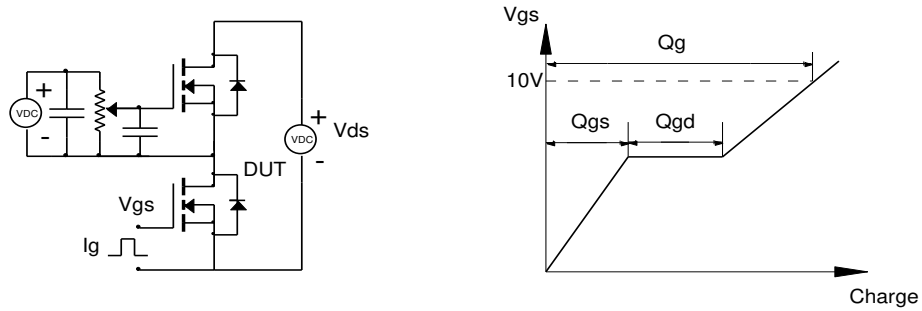
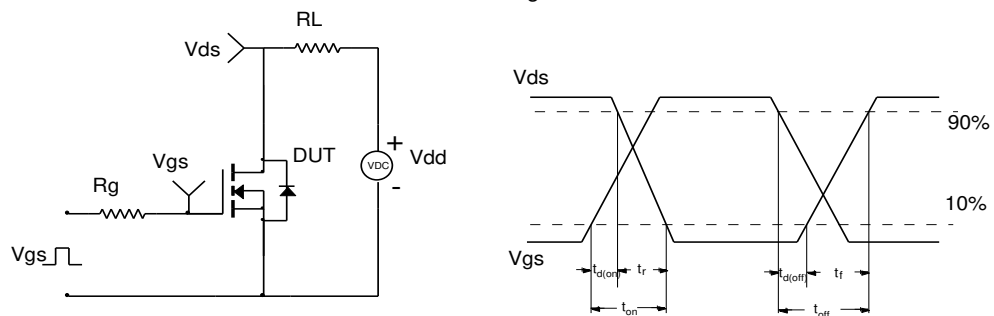


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

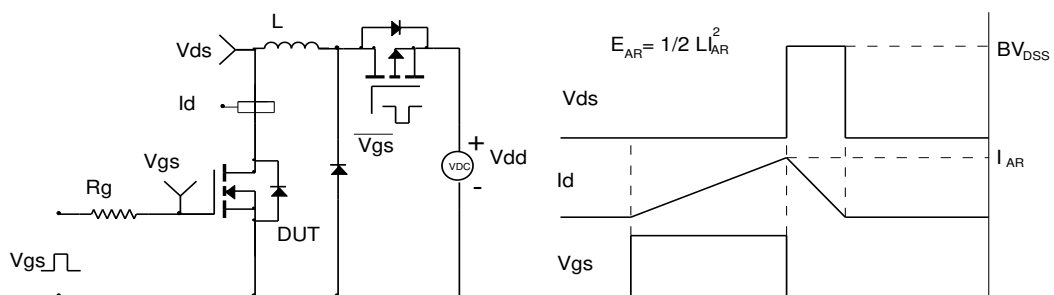
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

